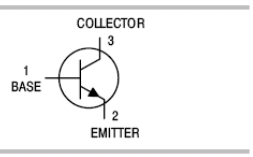
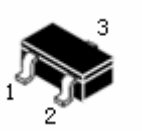
NPN Silicon Epitaxial Planar Transistor **KTC4076**

FEATURES

- Excellent H_{FE} Linearity.
- Complementary to KTA2015
- Power dissipation.(P_C=100mW)

Lead-free





SOT-323

APPLICATIONS

- General purpose and switching application.

ORDERING INFORMATION

Type No.	Marking	Package Code
KTC4076	WO/WY	SOT-323

MAXIMUM RATING @ Ta=25℃ unless otherwise specified

Symbol	**Parameter**	**Value**	**Units**
V_{CBO}	Collector-Base Voltage	35	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	500	mA
P_C	Collector Dissipation	100	mW
T_j,T_{stg}	Junction and Storage Temperature	-55~150	℃

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ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

Parameter	**Symbol**	**Test conditions**	**MIN**	**TYP**	**MAX**	**UNIT**
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=100μA,I_E=0	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA,I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=35V,I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V,I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE}=1V,I_C=100mA	70		240	
		V_{CE}=6V,I_C=400mA	25			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=100mA, I_B= 10mA		0.1	0.25	V
Transition frequency	f_T	V_{CE}=6V, I_C= 20mA				MHz
Collector output capacitance	C_{ob}	V_{CB}=6V, I_E=0mA f=1MHz		7.0		pF

CLASSIFICATION OF $h_{FE(1)}$

Range	O	Y
Marking	70-140	120-240

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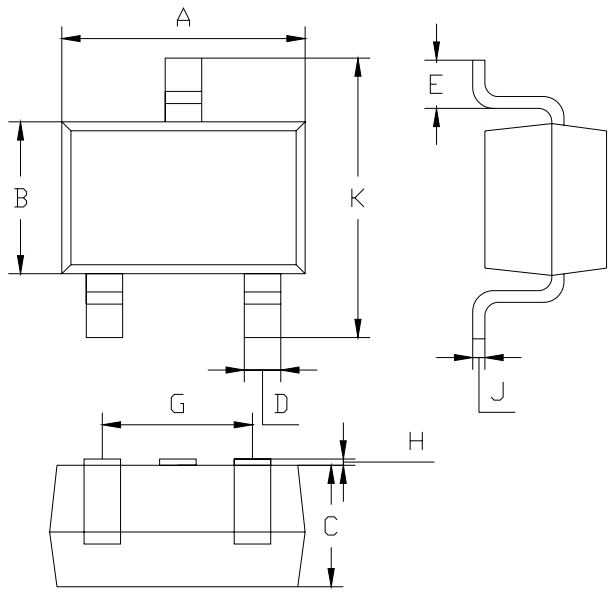
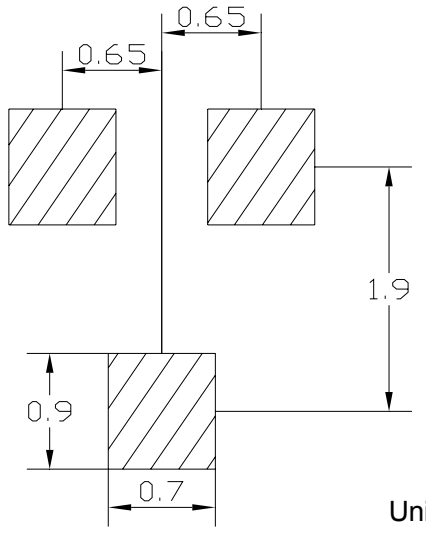
PACKAGE OUTLINE

Plastic surface mounted package SOT-323



SOT-323		
Dim	Min	Max
A	1.8	2.2
B	1.15	1.35
C	1.0Typical	
D	0.15	0.35
E	0.25	0.40
G	1.2	1.4
H	0.02	0.1
J	0.1Typical	
K	2.1	2.3
All Dimensions in mm		

SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
KTC4076	SOT-323	3000/Tape&Reel